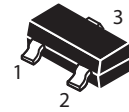
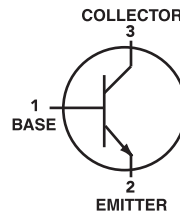


NPN General Purpose Transistors

(Pb) Lead(Pb)-Free



SOT-23

MAXIMUM RATINGS(Ta=25°C)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	35	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	800	mA
Total Device Dissipation $T_A=25^\circ\text{C}$	P_D	200	mW
Junction Temperature	T_j	+150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage $I_C = 0.1\text{mA}, I_B = 0$	$V_{(BR)CEO}$	30	-	-	V
Collector-Base Breakdown Voltage $I_C = 10\text{mA}, I_E = 0$	$V_{(BR)CBO}$	35	-	-	V
Emitter-Base Breakdown Voltage $I_E = 0.01\text{mA}, I_C = 0$	$V_{(BR)EBO}$	5.0	-	-	V
Collector Cutoff Current $V_{CB} = 35\text{V}, I_E = 0$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current $V_{EB} = 5\text{V}, I_C = 0$	I_{EBO}	-	-	0.1	μA

ON CHARACTERISTICS

Collector-Emitter Saturation Voltage $I_C = 500\text{mA}, I_B = 50\text{mA}$	$V_{CE(sat)}$	-	-	0.5	V
DC Current Transfer Ration $V_{CE} = 1\text{V}, I_C = 100\text{mA}$	h_{FE}	100	-	320	

SMALL-SIGNAL CHARACTERISTICS

Transition Frequency $V_{CE} = 5\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$	f_T	-	120	-	MHz
Collector Output Capacitance $V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	C_{ob}	-	13	-	pF

Classification of h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	FAO	FAY

Typica Characteristics

Fig. 1 $P_C - T_a$

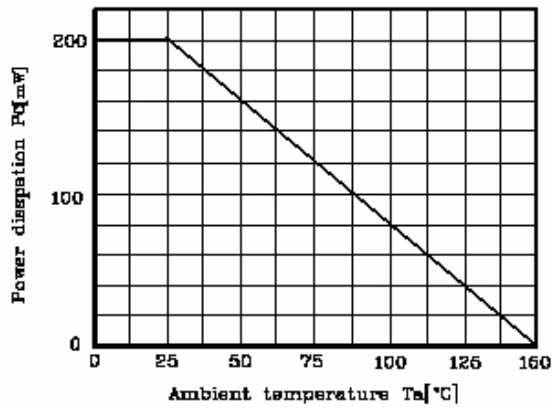


Fig. 2 $I_C - V_{BE}$

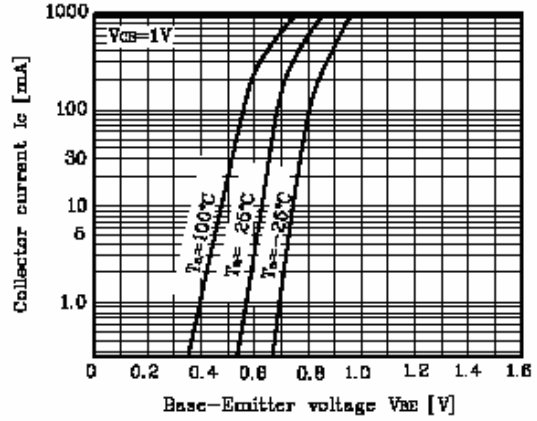


Fig. 3 $I_C - V_{CE}$

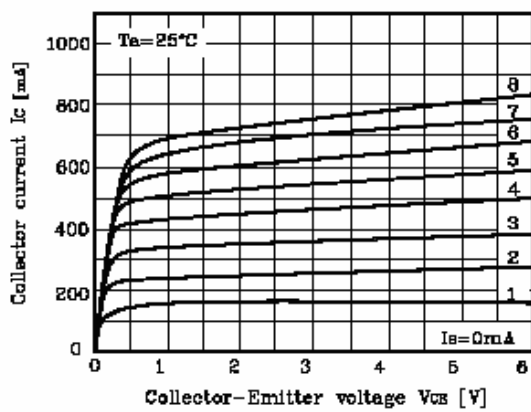


Fig. 4 $V_{CE(sat)} - I_C$

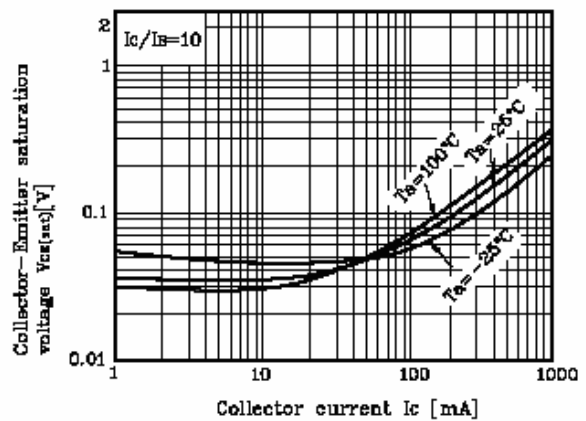
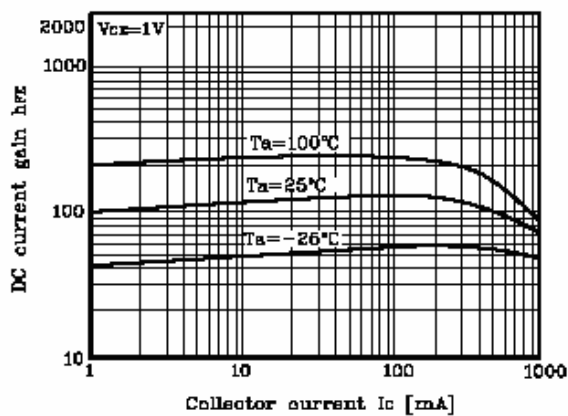
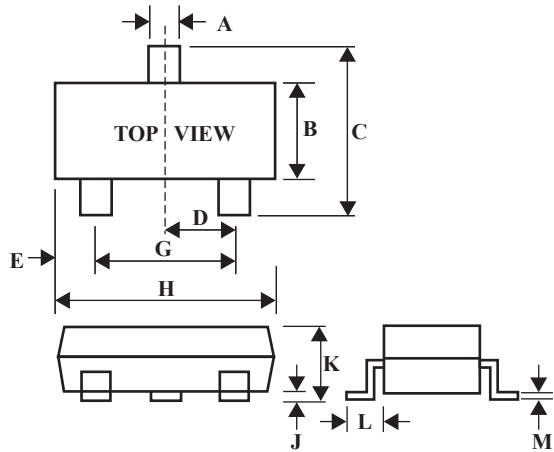


Fig. 5 $h_{FE} - I_C$



SOT-23 Outline Dimension



SOT-23		
Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25